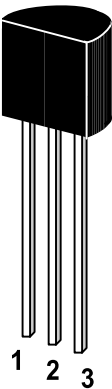


ST 2SA1024

PNP Silicon Epitaxial Planar Transistor
for high voltage applications.

The transistor is subdivided into two groups, O and Y
according to its DC current gain.

On special request, these transistors can be
manufactured in different pin configurations.



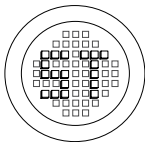
1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25°)

	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	150	V
Collector Emitter Voltage	-V _{CEO}	150	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	50	mA
Emitter Current	I _E	50	mA
Power Dissipation	P _{tot}	1000	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	-55 to +150	°C

G S P FORM A IS AVAILABLE



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РАДИОТЕХ

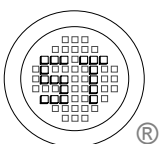
Тел.: (495) 795-0805
Факс: (495) 234-1603
Эл. почта: info@rct.ru
Веб: www.rct.ru

ST 2SA1024

Characteristics at $T_{amb}=25^{\circ}C$

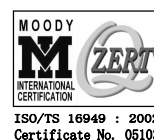
	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}=5V$, $-I_C=10mA$ Current Gain Group O Y	h_{FE}	70	-	140	-
	h_{FE}	120	-	240	-
Collector Cutoff Current at $-V_{CB}=150V$	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB}=5V$	$-I_{EBO}$	-	-	0.1	μA
Gain Bandwidth Product at $-V_{CE}=30V$, $-I_C=10mA$	f_T	-	120	-	MHz
Output Capacitance at $-V_{CB}=10V$, $f=1MHz$	C_{OB}	-	4	5	pF
Base Emitter Voltage at $-V_{CE}=5V$, $-I_C=30mA$	$-V_{BE}$	-	-	0.9	V
Collector Saturation Voltage at $-I_C=10mA$, $-I_B=1mA$	$-V_{CE(sat)}$	-	-	0.8	V

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SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, acompany
listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 07/12/2002